Altera - EPF10K30AQC208-2 Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

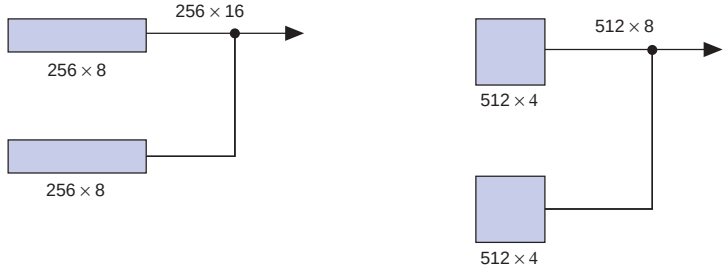
Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	216
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	147
Number of Gates	-
Voltage - Supply	3V ~ 3.6V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=epf10k30aqc208-2

Larger blocks of RAM are created by combining multiple EABs. For example, two 256 × 8 RAM blocks can be combined to form a 256 × 16 RAM block; two 512 × 4 blocks of RAM can be combined to form a 512 × 8 RAM block. See Figure 3.

Figure 3. Examples of Combining EABs



If necessary, all EABs in a device can be cascaded to form a single RAM block. EABs can be cascaded to form RAM blocks of up to 2,048 words without impacting timing. Altera's software automatically combines EABs to meet a designer's RAM specifications.

EABs provide flexible options for driving and controlling clock signals. Different clocks can be used for the EAB inputs and outputs. Registers can be independently inserted on the data input, EAB output, or the address and `WE` inputs. The global signals and the EAB local interconnect can drive the `WE` signal. The global signals, dedicated clock pins, and EAB local interconnect can drive the EAB clock signals. Because the LEs drive the EAB local interconnect, the LEs can control the `WE` signal or the EAB clock signals.

Each EAB is fed by a row interconnect and can drive out to row and column interconnects. Each EAB output can drive up to two row channels and up to two column channels; the unused row channel can be driven by other LEs. This feature increases the routing resources available for EAB outputs. See Figure 4.

Normal Mode

The normal mode is suitable for general logic applications and wide decoding functions that can take advantage of a cascade chain. In normal mode, four data inputs from the LAB local interconnect and the carry-in are inputs to a four-input LUT. The Compiler automatically selects the carry-in or the DATA3 signal as one of the inputs to the LUT. The LUT output can be combined with the cascade-in signal to form a cascade chain through the cascade-out signal. Either the register or the LUT can be used to drive both the local interconnect and the FastTrack Interconnect at the same time.

The LUT and the register in the LE can be used independently; this feature is known as register packing. To support register packing, the LE has two outputs; one drives the local interconnect and the other drives the FastTrack Interconnect. The DATA4 signal can drive the register directly, allowing the LUT to compute a function that is independent of the registered signal; a three-input function can be computed in the LUT, and a fourth independent signal can be registered. Alternatively, a four-input function can be generated, and one of the inputs to this function can be used to drive the register. The register in a packed LE can still use the clock enable, clear, and preset signals in the LE. In a packed LE, the register can drive the FastTrack Interconnect while the LUT drives the local interconnect, or vice versa.

Arithmetic Mode

The arithmetic mode offers 2 three-input LUTs that are ideal for implementing adders, accumulators, and comparators. One LUT computes a three-input function, and the other generates a carry output. As shown in Figure 9 on page 19, the first LUT uses the carry-in signal and two data inputs from the LAB local interconnect to generate a combinatorial or registered output. For example, in an adder, this output is the sum of three signals: a, b, and carry-in. The second LUT uses the same three signals to generate a carry-out signal, thereby creating a carry chain. The arithmetic mode also supports simultaneous use of the cascade chain.

FastTrack Interconnect

In the FLEX 10K architecture, connections between LEs and device I/O pins are provided by the FastTrack Interconnect, which is a series of continuous horizontal and vertical routing channels that traverse the device. This global routing structure provides predictable performance, even in complex designs. In contrast, the segmented routing in FPGAs requires switch matrices to connect a variable number of routing paths, increasing the delays between logic resources and reducing performance.

The FastTrack Interconnect consists of row and column interconnect channels that span the entire device. Each row of LABs is served by a dedicated row interconnect. The row interconnect can drive I/O pins and feed other LABs in the device. The column interconnect routes signals between rows and can drive I/O pins.

A row channel can be driven by an LE or by one of three column channels. These four signals feed dual 4-to-1 multiplexers that connect to two specific row channels. These multiplexers, which are connected to each LE, allow column channels to drive row channels even when all eight LEs in an LAB drive the row interconnect.

Each column of LABs is served by a dedicated column interconnect. The column interconnect can then drive I/O pins or another row's interconnect to route the signals to other LABs in the device. A signal from the column interconnect, which can be either the output of an LE or an input from an I/O pin, must be routed to the row interconnect before it can enter an LAB or EAB. Each row channel that is driven by an IOE or EAB can drive one specific column channel.

Access to row and column channels can be switched between LEs in adjacent pairs of LABs. For example, an LE in one LAB can drive the row and column channels normally driven by a particular LE in the adjacent LAB in the same row, and vice versa. This routing flexibility enables routing resources to be used more efficiently. See Figure 11.

I/O Element

An I/O element (IOE) contains a bidirectional I/O buffer and a register that can be used either as an input register for external data that requires a fast setup time, or as an output register for data that requires fast clock-to-output performance. In some cases, using an LE register for an input register will result in a faster setup time than using an IOE register. IOEs can be used as input, output, or bidirectional pins. For bidirectional registered I/O implementation, the output register should be in the IOE and, the data input and output enable register should be LE registers placed adjacent to the bidirectional pin. The Compiler uses the programmable inversion option to invert signals from the row and column interconnect automatically where appropriate. Figure 13 shows the bidirectional I/O registers.

Each IOE selects the clock, clear, clock enable, and output enable controls from a network of I/O control signals called the peripheral control bus. The peripheral control bus uses high-speed drivers to minimize signal skew across devices; it provides up to 12 peripheral control signals that can be allocated as follows:

- Up to eight output enable signals
- Up to six clock enable signals
- Up to two clock signals
- Up to two clear signals

If more than six clock enable or eight output enable signals are required, each IOE on the device can be controlled by clock enable and output enable signals driven by specific LEs. In addition to the two clock signals available on the peripheral control bus, each IOE can use one of two dedicated clock pins. Each peripheral control signal can be driven by any of the dedicated input pins or the first LE of each LAB in a particular row. In addition, an LE in a different row can drive a column interconnect, which causes a row interconnect to drive the peripheral control signal. The chip-wide reset signal will reset all IOE registers, overriding any other control signals.

Tables 8 and 9 list the sources for each peripheral control signal, and the rows that can drive global signals. These tables also show how the output enable, clock enable, clock, and clear signals share 12 peripheral control signals.

Signals on the peripheral control bus can also drive the four global signals, referred to as GLOBAL0 through GLOBAL3 in Tables 8 and 9. The internally generated signal can drive the global signal, providing the same low-skew, low-delay characteristics for an internally generated signal as for a signal driven by an input. This feature is ideal for internally generated clear or clock signals with high fan-out. When a global signal is driven by internal logic, the dedicated input pin that drives that global signal cannot be used. The dedicated input pin should be driven to a known logic state (such as ground) and not be allowed to float.

When the chip-wide output enable pin is held low, it will tri-state all pins on the device. This option can be set in the Global Project Device Options menu. Additionally, the registers in the IOE can be reset by holding the chip-wide reset pin low.

Row-to-IOE Connections

When an IOE is used as an input signal, it can drive two separate row channels. The signal is accessible by all LEs within that row. When an IOE is used as an output, the signal is driven by a multiplexer that selects a signal from the row channels. Up to eight IOEs connect to each side of each row channel. See Figure 14.

Figure 14. FLEX 10K Row-to-IOE Connections

The values for m and n are provided in Table 10.

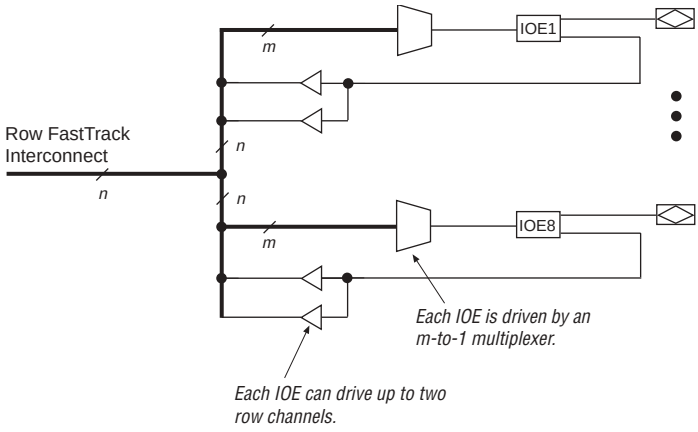


Table 15. 32-Bit FLEX 10K Device IDCODE *Note (1)*

Device	IDCODE (32 Bits)			
	Version (4 Bits)	Part Number (16 Bits)	Manufacturer's Identity (11 Bits)	1 (1 Bit) *(2)*
EPF10K10, EPF10K10A	0000	0001 0000 0001 0000	00001101110	1
EPF10K20	0000	0001 0000 0010 0000	00001101110	1
EPF10K30, EPF10K30A	0000	0001 0000 0011 0000	00001101110	1
EPF10K40	0000	0001 0000 0100 0000	00001101110	1
EPF10K50, EPF10K50V	0000	0001 0000 0101 0000	00001101110	1
EPF10K70	0000	0001 0000 0111 0000	00001101110	1
EPF10K100, EPF10K100A	0000	0000 0001 0000 0000	00001101110	1
EPF10K130V	0000	0000 0001 0011 0000	00001101110	1
EPF10K250A	0000	0000 0010 0101 0000	00001101110	1

Notes:
(1) The most significant bit (MSB) is on the left.
(2) The least significant bit (LSB) for all JTAG IDCODEs is 1.

FLEX 10K devices include weak pull-ups on JTAG pins.

For more information, see the following documents:

- *Application Note 39 (IEEE 1149.1 (JTAG) Boundary-Scan Testing in Altera Devices)*
- *BitBlaster Serial Download Cable Data Sheet*
- *ByteBlasterMV Parallel Port Download Cable Data Sheet*
- *Jam Programming & Test Language Specification*

Table 18. FLEX 10K 5.0-V Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	4.75 (4.50)	5.25 (5.50)	V
V_{CCIO}	Supply voltage for output buffers, 5.0-V operation	*(3)*, *(4)*	4.75 (4.50)	5.25 (5.50)	V
	Supply voltage for output buffers, 3.3-V operation	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
V_I	Input voltage		–0.5	V_{CCINT} + 0.5	V
V_O	Output voltage		0	V_{CCIO}	V
T_A	Ambient temperature	For commercial use	0	70	° C
		For industrial use	–40	85	° C
T_J	Operating temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Notes to tables:

(1) See the *Operating Requirements for Altera Devices Data Sheet*.
(2) Minimum DC input voltage is –0.5 V. During transitions, the inputs may undershoot to –2.0 V for input currents less than 100 mA and periods shorter than 20 ns.
(3) Numbers in parentheses are for industrial-temperature-range devices.
(4) Maximum V_{CC} rise time is 100 ms. V_{CC} must rise monotonically.
(5) Typical values are for T_A = 25° C and V_{CC} = 5.0 V.
(6) These values are specified under the Recommended Operation Condition shown in Table 18 on page 45.
(7) The I_{OH} parameter refers to high-level TTL or CMOS output current.
(8) The I_{OL} parameter refers to low-level TTL or CMOS output current. This parameter applies to open-drain pins as well as output pins.
(9) This value is specified for normal device operation. The value may vary during power-up.
(10) Capacitance is sample-tested only.

Figure 20 shows the typical output drive characteristics of FLEX 10K devices with 5.0-V and 3.3-V V_{CCIO}. The output driver is compliant with the 5.0-V ***PCI Local Bus Specification, Revision 2.2*** (for 5.0-V V_{CCIO}).

Figure 20. Output Drive Characteristics of FLEX 10K Devices

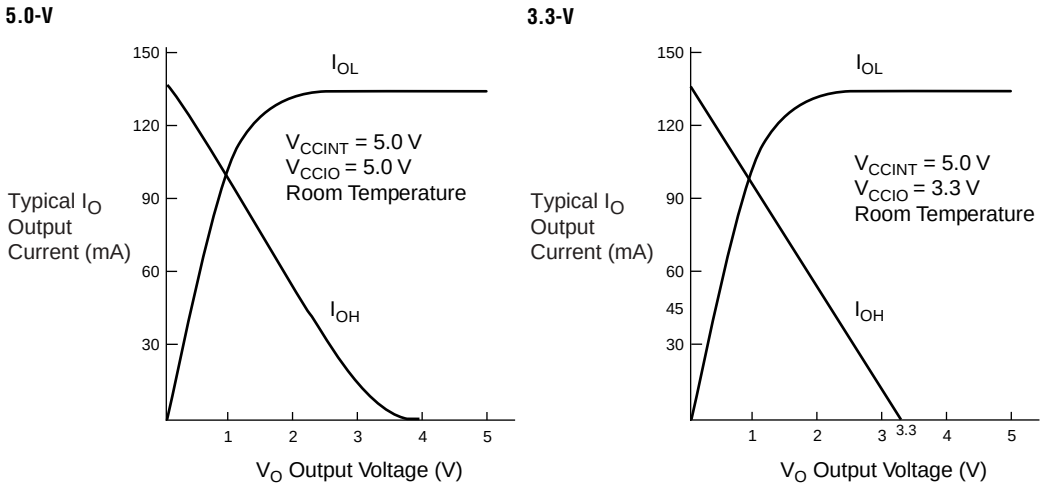


Figure 26. FLEX 10K Device IOE Timing Model

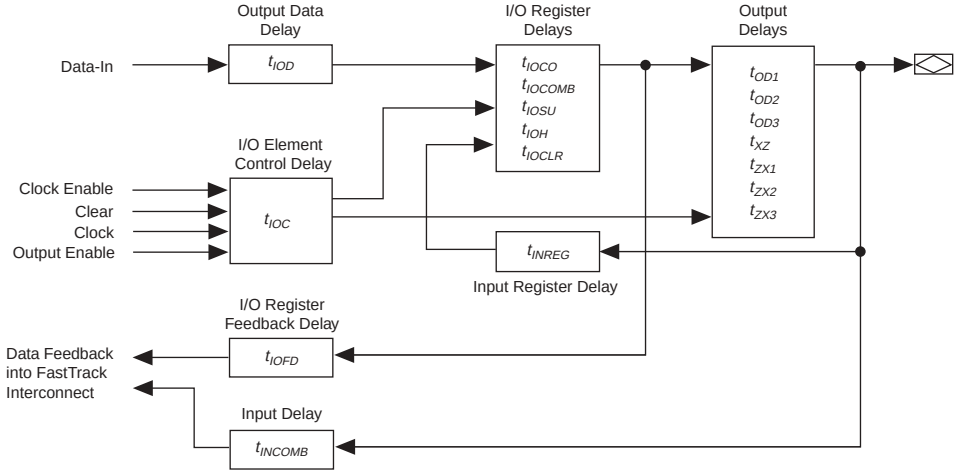
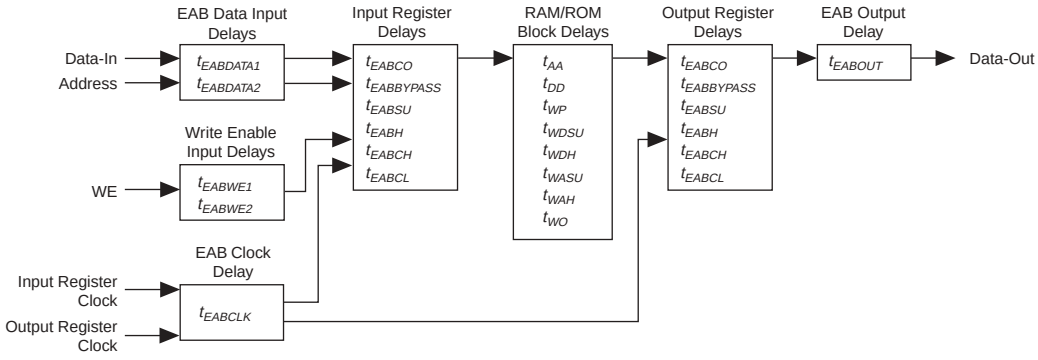


Figure 27. FLEX 10K Device EAB Timing Model



Figures 28 shows the timing model for bidirectional I/O pin timing.

Table 32. LE Timing Microparameters (Part 2 of 2) *Note (1)*

Symbol	Parameter	Conditions
t_{SU}	LE register setup time for data and enable signals before clock; LE register recovery time after asynchronous clear, preset, or load	
t_{H}	LE register hold time for data and enable signals after clock	
t_{PRE}	LE register preset delay	
t_{CLR}	LE register clear delay	
t_{CH}	Minimum clock high time from clock pin	
t_{CL}	Minimum clock low time from clock pin	

Table 33. IOE Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
t_{IOD}	IOE data delay	
t_{IOC}	IOE register control signal delay	
t_{IOCO}	IOE register clock-to-output delay	
t_{IOCOMB}	IOE combinatorial delay	
t_{IOSU}	IOE register setup time for data and enable signals before clock; IOE register recovery time after asynchronous clear	
t_{IOH}	IOE register hold time for data and enable signals after clock	
t_{IOCLR}	IOE register clear time	
t_{OD1}	Output buffer and pad delay, slow slew rate = off, $V_{CCIO} = V_{CCINT}$	C1 = 35 pF *(2)*
t_{OD2}	Output buffer and pad delay, slow slew rate = off, V_{CCIO} = low voltage	C1 = 35 pF *(3)*
t_{OD3}	Output buffer and pad delay, slow slew rate = on	C1 = 35 pF *(4)*
t_{XZ}	IOE output buffer disable delay	
t_{ZX1}	IOE output buffer enable delay, slow slew rate = off, $V_{CCIO} = V_{CCINT}$	C1 = 35 pF *(2)*
t_{ZX2}	IOE output buffer enable delay, slow slew rate = off, V_{CCIO} = low voltage	C1 = 35 pF *(3)*
t_{ZX3}	IOE output buffer enable delay, slow slew rate = on	C1 = 35 pF *(4)*
t_{INREG}	IOE input pad and buffer to IOE register delay	
t_{IOFD}	IOE register feedback delay	
t_{INCOMB}	IOE input pad and buffer to FastTrack Interconnect delay	

Table 36. Interconnect Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
$t_{DIN2IOE}$	Delay from dedicated input pin to IOE control input	*(7)*
$t_{DCLK2LE}$	Delay from dedicated clock pin to LE or EAB clock	*(7)*
$t_{DIN2DATA}$	Delay from dedicated input or clock to LE or EAB data	*(7)*
$t_{DCLK2IOE}$	Delay from dedicated clock pin to IOE clock	*(7)*
t_{DIN2LE}	Delay from dedicated input pin to LE or EAB control input	*(7)*
$t_{SAMELAB}$	Routing delay for an LE driving another LE in the same LAB	
$t_{SAMEROW}$	Routing delay for a row IOE, LE, or EAB driving a row IOE, LE, or EAB in the same row	*(7)*
$t_{SAMECOLUMN}$	Routing delay for an LE driving an IOE in the same column	*(7)*
$t_{DIFFROW}$	Routing delay for a column IOE, LE, or EAB driving an LE or EAB in a different row	*(7)*
$t_{TWOROWS}$	Routing delay for a row IOE or EAB driving an LE or EAB in a different row	*(7)*
$t_{LEPERIPH}$	Routing delay for an LE driving a control signal of an IOE via the peripheral control bus	*(7)*
$t_{LABCARRY}$	Routing delay for the carry-out signal of an LE driving the carry-in signal of a different LE in a different LAB	
$t_{LABCASC}$	Routing delay for the cascade-out signal of an LE driving the cascade-in signal of a different LE in a different LAB	

Table 37. External Timing Parameters *Notes (8), (10)*

Symbol	Parameter	Conditions
t_{DRR}	Register-to-register delay via four LEs, three row interconnects, and four local interconnects	*(9)*
t_{INSU}	Setup time with global clock at IOE register	
t_{INH}	Hold time with global clock at IOE register	
t_{OUTCO}	Clock-to-output delay with global clock at IOE register	

Table 38. External Bidirectional Timing Parameters *Note (10)*

Symbol	Parameter	Condition
$t_{INSUBIDIR}$	Setup time for bidirectional pins with global clock at adjacent LE register	
$t_{INHBIDIR}$	Hold time for bidirectional pins with global clock at adjacent LE register	
$t_{OUTCOBIDIR}$	Clock-to-output delay for bidirectional pins with global clock at IOE register	
$t_{XZBIDIR}$	Synchronous IOE output buffer disable delay	
$t_{ZXBIDIR}$	Synchronous IOE output buffer enable delay, slow slew rate = off	

Notes to tables:

(1) Microparameters are timing delays contributed by individual architectural elements. These parameters cannot be measured explicitly.

(2) Operating conditions: V_{CCIO} = 5.0 V ± 5% for commercial use in FLEX 10K devices.
V_{CCIO} = 5.0 V ± 10% for industrial use in FLEX 10K devices.
V_{CCIO} = 3.3 V ± 10% for commercial or industrial use in FLEX 10KA devices.

(3) Operating conditions: V_{CCIO} = 3.3 V ± 10% for commercial or industrial use in FLEX 10K devices.
V_{CCIO} = 2.5 V ± 0.2 V for commercial or industrial use in FLEX 10KA devices.

(4) Operating conditions: V_{CCIO} = 2.5 V, 3.3 V, or 5.0 V.

(5) Because the RAM in the EAB is self-timed, this parameter can be ignored when the WE signal is registered.

(6) EAB macroparameters are internal parameters that can simplify predicting the behavior of an EAB at its boundary; these parameters are calculated by summing selected microparameters.

(7) These parameters are worst-case values for typical applications. Post-compilation timing simulation and timing analysis are required to determine actual worst-case performance.

(8) External reference timing parameters are factory-tested, worst-case values specified by Altera. A representative subset of signal paths is tested to approximate typical device applications.

(9) Contact Altera Applications for test circuit specifications and test conditions.

(10) These timing parameters are sample-tested only.

Figures 29 and 30 show the asynchronous and synchronous timing waveforms, respectively, for the EAB macroparameters in Table 34.

Figure 29. EAB Asynchronous Timing Waveforms

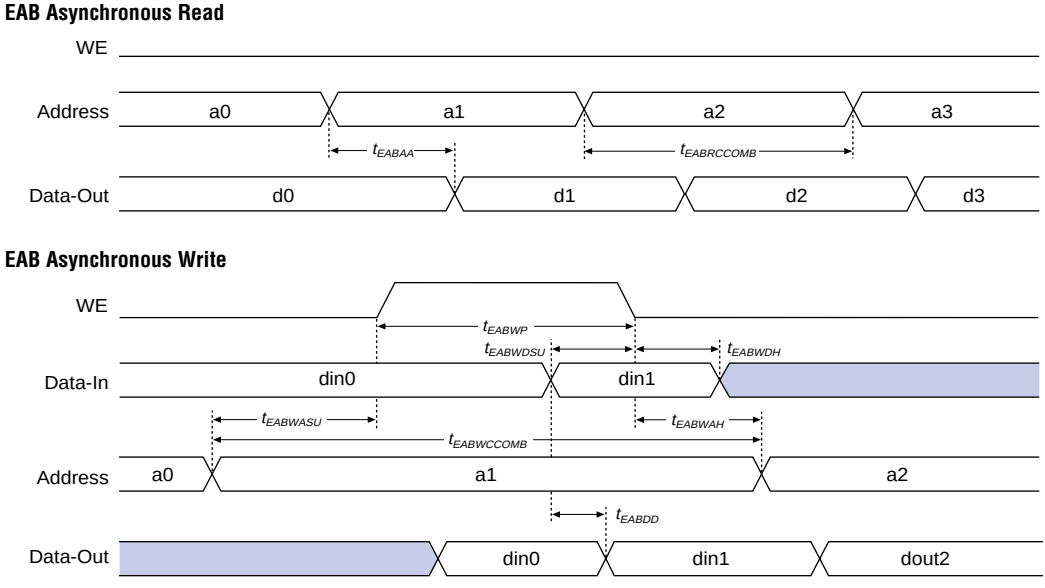


Table 59. EPF10K70 Device EAB Internal Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.3		1.5		1.9	ns
$t_{EABDATA2}$		4.3		4.8		6.0	ns
t_{EABWE1}		0.9		1.0		1.2	ns
t_{EABWE2}		4.5		5.0		6.2	ns
t_{EABCLK}		0.9		1.0		2.2	ns
t_{EABCO}		0.4		0.5		0.6	ns
$t_{EABBYPASS}$		1.3		1.5		1.9	ns
t_{EABSU}	1.3		1.5		1.8		ns
t_{EABH}	1.8		2.0		2.5		ns
t_{AA}		7.8		8.7		10.7	ns
t_{WP}	5.2		5.8		7.2		ns
t_{WDSU}	1.4		1.6		2.0		ns
t_{WDH}	0.3		0.3		0.4		ns
t_{WASU}	0.4		0.5		0.6		ns
t_{WAH}	0.9		1.0		1.2		ns
t_{WO}		4.5		5.0		6.2	ns
t_{DD}		4.5		5.0		6.2	ns
t_{EABOUT}		0.4		0.5		0.6	ns
t_{EABCH}	4.0		4.0		4.0		ns
t_{EABCL}	5.2		5.8		7.2		ns

Table 66. EPF10K100 Device EAB Internal Microparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.5		1.5		1.9	ns
$t_{EABDATA2}$		4.8		4.8		6.0	ns
t_{EABWE1}		1.0		1.0		1.2	ns
t_{EABWE2}		5.0		5.0		6.2	ns
t_{EABCLK}		1.0		1.0		2.2	ns
t_{EABCO}		0.5		0.5		0.6	ns
$t_{EABBYPASS}$		1.5		1.5		1.9	ns
t_{EABSU}	1.5		1.5		1.8		ns
t_{EABH}	2.0		2.0		2.5		ns
t_{AA}		8.7		8.7		10.7	ns
t_{WP}	5.8		5.8		7.2		ns
t_{WDSU}	1.6		1.6		2.0		ns
t_{WDH}	0.3		0.3		0.4		ns
t_{WASU}	0.5		0.5		0.6		ns
t_{WAH}	1.0		1.0		1.2		ns
t_{WO}		5.0		5.0		6.2	ns
t_{DD}		5.0		5.0		6.2	ns
t_{EABOUT}		0.5		0.5		0.6	ns
t_{EABCH}	4.0		4.0		4.0		ns
t_{EABCL}	5.8		5.8		7.2		ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 85 through 91 show EPF10K10A device internal and external timing parameters.

Table 85. EPF10K10A Device LE Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.9		1.2		1.6	ns
t_{CLUT}		1.2		1.4		1.9	ns
t_{RLUT}		1.9		2.3		3.0	ns
t_{PACKED}		0.6		0.7		0.9	ns
t_{EN}		0.5		0.6		0.8	ns
t_{CICO}		02		0.3		0.4	ns
t_{CGEN}		0.7		0.9		1.1	ns
t_{CGENR}		0.7		0.9		1.1	ns
t_{CASC}		1.0		1.2		1.7	ns
t_{C}		1.2		1.4		1.9	ns
t_{CO}		0.5		0.6		0.8	ns
t_{COMB}		0.5		0.6		0.8	ns
t_{SU}	1.1		1.3		1.7		ns
t_{H}	0.6		0.7		0.9		ns
t_{PRE}		0.5		0.6		0.9	ns
t_{CLR}		0.5		0.6		0.9	ns
t_{CH}	3.0		3.5		4.0		ns
t_{CL}	3.0		3.5		4.0		ns

Table 86. EPF10K10A Device IOE Timing Microparameters *Note (1)* **(Part 1 of 2)**

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
		1.3		1.5		2.0	ns
t_{IOC}		0.2		0.3		0.3	ns
t_{IOCO}		0.2		0.3		0.4	ns
t_{IOCOMB}		0.6		0.7		0.9	ns
t_{IOSU}	0.8		1.0		1.3		ns

Table 86. EPF10K10A Device IOE Timing Microparameters *Note (1)* *(Part 2 of 2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOH}	0.8		1.0		1.3		ns
t_{IOCLR}		1.2		1.4		1.9	ns
t_{OD1}		1.2		1.4		1.9	ns
t_{OD2}		2.9		3.5		4.7	ns
t_{OD3}		6.6		7.8		10.5	ns
t_{XZ}		1.2		1.4		1.9	ns
t_{ZX1}		1.2		1.4		1.9	ns
t_{ZX2}		2.9		3.5		4.7	ns
t_{ZX3}		6.6		7.8		10.5	ns
t_{INREG}		5.2		6.3		8.4	ns
t_{IOFD}		3.1		3.8		5.0	ns
t_{INCOMB}		3.1		3.8		5.0	ns

Table 87. EPF10K10A Device EAB Internal Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		3.3		3.9		5.2	ns
$t_{EABDATA2}$		1.0		1.3		1.7	ns
t_{EABWE1}		2.6		3.1		4.1	ns
t_{EABWE2}		2.7		3.2		4.3	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		1.2		1.4		1.8	ns
$t_{EABBYPASS}$		0.1		0.2		0.2	ns
t_{EABSU}	1.4		1.7		2.2		ns
t_{EABH}	0.1		0.1		0.1		ns
t_{AA}		4.5		5.4		7.3	ns
t_{WP}	2.0		2.4		3.2		ns
t_{WDSU}	0.7		0.8		1.1		ns
t_{WDH}	0.5		0.6		0.7		ns
t_{WASU}	0.6		0.7		0.9		ns
t_{WAH}	0.9		1.1		1.5		ns
t_{WO}		3.3		3.9		5.2	ns
t_{DD}		3.3		3.9		5.2	ns
t_{EABOUT}		0.1		0.1		0.2	ns
t_{EABCH}	3.0		3.5		4.0		ns
t_{EABCL}	3.03		3.5		4.0		ns

$\mathbf{f_{MAX}}$ = Maximum operating frequency in MHz
N = Total number of logic cells used in the device
$\mathbf{tog_{LC}}$ = Average percent of logic cells toggling at each clock (typically 12.5%)
K = Constant, shown in Tables 114 and 115

Table 114. FLEX 10K K Constant Values

Device	K Value
EPF10K10	82
EPF10K20	89
EPF10K30	88
EPF10K40	92
EPF10K50	95
EPF10K70	85
EPF10K100	88

Table 115. FLEX 10KA K Constant Values

Device	K Value
EPF10K10A	17
EPF10K30A	17
EPF10K50V	19
EPF10K100A	19
EPF10K130V	22
EPF10K250A	23

This calculation provides an I_{CC} estimate based on typical conditions with no output load. The actual I_{CC} should be verified during operation because this measurement is sensitive to the actual pattern in the device and the environmental operating conditions.

To better reflect actual designs, the power model (and the constant *K* in the power calculation equations) for continuous interconnect FLEX devices assumes that logic cells drive FastTrack Interconnect channels. In contrast, the power model of segmented FPGAs assumes that all logic cells drive only one short interconnect segment. This assumption may lead to inaccurate results, compared to measured power consumption for an actual design in a segmented interconnect FPGA.

Figure 32 shows the relationship between the current and operating frequency of FLEX 10K devices.

SRAM configuration elements allow FLEX 10K devices to be reconfigured in-circuit by loading new configuration data into the device. Real-time reconfiguration is performed by forcing the device into command mode with a device pin, loading different configuration data, reinitializing the device, and resuming user-mode operation.

The entire reconfiguration process may be completed in less than 320 ms using an EPF10K250A device with a DCLK frequency of 10 MHz. This process can be used to reconfigure an entire system dynamically. In-field upgrades can be performed by distributing new configuration files.

Refer to the configuration device data sheet to obtain the POR delay when using a configuration device method.

Programming Files

Despite being function- and pin-compatible, FLEX 10KA and FLEX 10KE devices are not programming- or configuration-file compatible with FLEX 10K devices. A design should be recompiled before it is transferred from a FLEX 10K device to an equivalent FLEX 10KA or FLEX 10KE device. This recompilation should be performed to create a new programming or configuration file and to check design timing on the faster FLEX 10KA or FLEX 10KE device. The programming or configuration files for EPF10K50 devices can program or configure an EPF10K50V device. However, Altera recommends recompiling a design for the EPF10K50V device when transferring it from the EPF10K50 device.

Configuration Schemes

The configuration data for a FLEX 10K device can be loaded with one of five configuration schemes (see Table 116), chosen on the basis of the target application. An EPC1, EPC2, EPC16, or EPC1441 configuration device, intelligent controller, or the JTAG port can be used to control the configuration of a FLEX 10K device, allowing automatic configuration on system power-up.